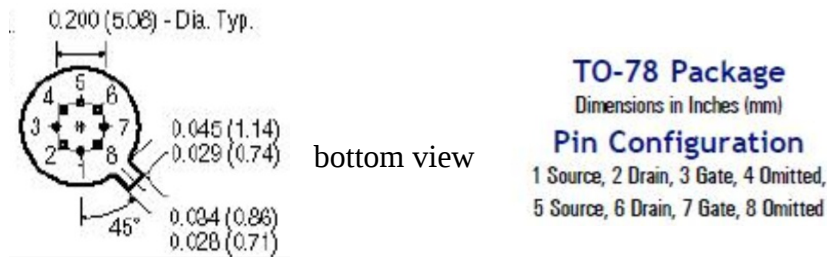


$I_d$  vs  $V_{gs}$  measured at  $V_{ds} = 4V$ , drain current limited to 80/90 mA  
measured with HP6633B power supply vor  $V_{dd}$  and R&S NGT20 for gate voltage.  
Sorry, no curve tracer here.



$V_{gs}$	Q1-567	Q1-123	Q2-567	Q2-123	Q3-567	Q3-123	Q4-567	Q4-123
-2	0,0	0,0	0,0	0,0	0,0	0,0	0,0	0,0
-1	0,0	0,0	0,0	0,0	0,0	0,0	0,0	0,0
-0,8	0,1	0,1	0,0	0,0	0,1	0,1	0,0	0,3
-0,7	1,0	1,1	0,0	0,0	1,5	1,6	6,2	3,3
-0,6	6,4	6,8	0,1	0,0	8,9	8,9	19,6	13,3
-0,5	21,5	22,2	1,2	0,2	25,1	24,5	40,3	31,6
-0,4	39,6	40,6	7,2	1,2	50,4	48,3	68,3	57,6
-0,3	67,5	69,2	25	8,7	78,6	75,3	85	85
-0,2	85,0	85,0	49,2	25,1	85	85	85	85
-0,1	85,0	85,0	85,0	52,9	85	85	85	85
-0,05	85,0	85,0	85,0	67	85	85	85	85
-0,0	85,0	85,0	85,0	82	85	85	85	85

85 mA is not verbatim, it means that the current limit of the power supply has been reached.  
82 mA is true  $I_{dss}$  for Q2-123.

Conclusion: Q1 and Q3 are somewhat similar, Q2 is the laziest, Q4 is the steepest.  
Q2 pair has 100mV offset.

Bias resistor	FETs: 1/2 IF3602	FETs: 2/2 IF3602	FETs: 4/2 IF3602
	$I_{dd}$ / GateVoltage	$I_{dd}$ / GateVoltage	$I_{dd}$ / GateVoltage
open	0.2 mA		
2K5	5.6 mA		
470R	25.89 mA / -0.482 V	25.89 mA / -0.616 V	25.89 mA / -0.67V
330R (42 mA)	36.8 mA		36.72 mA @150+180R
270R	44.7 mA		

330R was split into 150 + 180 later because of heat.